

# SN54ABT827, SN74ABT827 10-BIT BUFFERS/DRIVERS WITH 3-STATE OUTPUTS

SCBS159D – JANUARY 1991 – REVISED MAY 1997

- State-of-the-Art *EPIC-IIB™* BiCMOS Design Significantly Reduces Power Dissipation
- Flow-Through Architecture Optimizes PCB Layout
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Typical  $V_{OLP}$  (Output Ground Bounce) < 1 V at  $V_{CC} = 5$  V,  $T_A = 25^\circ\text{C}$
- High-Impedance State During Power Up and Power Down
- High-Drive Outputs ( $-32\text{-mA } I_{OH}$ ,  $64\text{-mA } I_{OL}$ )
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), and Plastic (NT) and Ceramic (JT) DIPs

## description

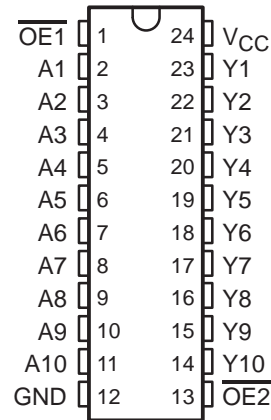
These 10-bit buffers or bus drivers provide a high-performance bus interface for wide data paths or buses carrying parity.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable ( $\overline{OE1}$  or  $\overline{OE2}$ ) input is high, all ten outputs are in the high-impedance state. The 'ABT827 provide true data at the outputs.

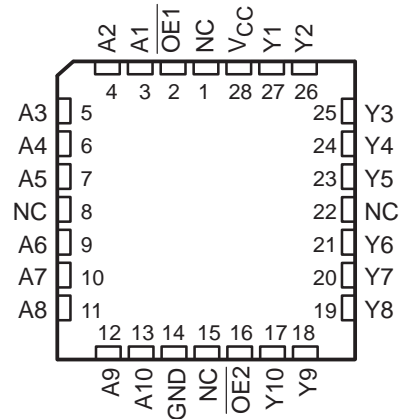
When  $V_{CC}$  is between 0 and 2.1 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 2.1 V,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54ABT827 is characterized for operation over the full military temperature range of  $-55^\circ\text{C}$  to  $125^\circ\text{C}$ . The SN74ABT827 is characterized for operation from  $-40^\circ\text{C}$  to  $85^\circ\text{C}$ .

SN54ABT827 . . . JT PACKAGE  
SN74ABT827 . . . DB, DW, NT, OR PW PACKAGE  
(TOP VIEW)



SN54ABT827 . . . FK PACKAGE  
(TOP VIEW)



NC – No internal connection

FUNCTION TABLE

INPUTS			OUTPUT
$\overline{OE1}$	$\overline{OE2}$	A	Y
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z



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**TEXAS  
INSTRUMENTS**

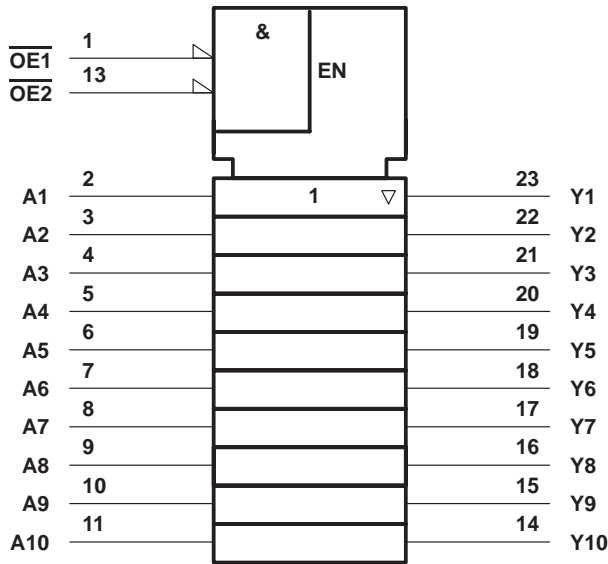
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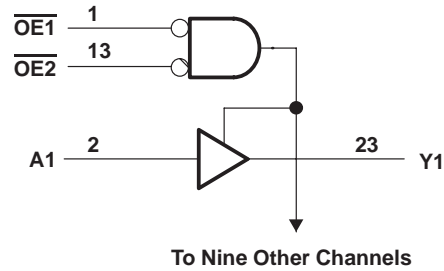
# SN54ABT827, SN74ABT827 10-BIT BUFFERS/DRIVERS WITH 3-STATE OUTPUTS

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## logic symbol†



## logic diagram (positive logic)



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.  
Pin numbers shown are for the DB, DW, JT, NT, and PW packages.

## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, $V_{CC}$ .....	-0.5 V to 7 V
Input voltage range, $V_I$ (see Note 1) .....	-0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, $V_O$ .....	-0.5 V to 5.5 V
Current into any output in the low state, $I_O$ : SN54ABT827 .....	96 mA
SN74ABT827 .....	128 mA
Input clamp current, $I_{IK}$ ( $V_I < 0$ ) .....	-18 mA
Output clamp current, $I_{OK}$ ( $V_O < 0$ ) .....	-50 mA
Package thermal impedance, $\theta_{JA}$ (see Note 2): DB package .....	104°C/W
DW package .....	81°C/W
NT package .....	67°C/W
PW package .....	120°C/W
Storage temperature range, $T_{stg}$ .....	-65°C to 150°C

‡ Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.  
2. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51, except for through-hole packages, which use a trace length of zero.

**SN54ABT827, SN74ABT827**  
**10-BIT BUFFERS/DRIVERS**  
**WITH 3-STATE OUTPUTS**

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**recommended operating conditions (see Note 3)**

		SN54ABT827		SN74ABT827		UNIT
		MIN	MAX	MIN	MAX	
V <sub>CC</sub>	Supply voltage	4.5	5.5	4.5	5.5	V
V <sub>IH</sub>	High-level input voltage	2		2		V
V <sub>IL</sub>	Low-level input voltage		0.8		0.8	V
V <sub>I</sub>	Input voltage	0	V <sub>CC</sub>	0	V <sub>CC</sub>	V
I <sub>OH</sub>	High-level output current		-24		-32	mA
I <sub>OL</sub>	Low-level output current		48		64	mA
Δt/Δv	Input transition rise or fall rate		5		5	ns/V
Δt/ΔV <sub>CC</sub>	Power-up ramp rate	200		200		μs/V
T <sub>A</sub>	Operating free-air temperature	-55	125	-40	85	°C

NOTE 3: Unused inputs must be held high or low to prevent them from floating.

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**10-BIT BUFFERS/DRIVERS**  
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**electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)**

PARAMETER	TEST CONDITIONS	T <sub>A</sub> = 25°C			SN54ABT827		SN74ABT827		UNIT
		MIN	TYP†	MAX	MIN	MAX	MIN	MAX	
V <sub>IK</sub>	V <sub>CC</sub> = 4.5 V, I <sub>I</sub> = -18 mA			-1.2		-1.2		-1.2	V
V <sub>OH</sub>	V <sub>CC</sub> = 4.5 V, I <sub>OH</sub> = -3 mA	2.5			2.5		2.5		V
	V <sub>CC</sub> = 5 V, I <sub>OH</sub> = -3 mA	3			3		3		
	V <sub>CC</sub> = 4.5 V, I <sub>OH</sub> = -24 mA	2			2				
V <sub>OL</sub>	V <sub>CC</sub> = 4.5 V, I <sub>OL</sub> = 48 mA			0.55		0.55			V
				0.55*			0.55		
V <sub>hys</sub>			100					mV	
I <sub>I</sub>	V <sub>CC</sub> = 0 to 5.5 V, V <sub>I</sub> = V <sub>CC</sub> or GND			±1		±1		±1	µA
I <sub>OZPU</sub> ‡	V <sub>CC</sub> = 0 to 2.1 V, V <sub>O</sub> = 0.5 V to 2.7 V, $\overline{OE} = X$			±50		±10		±50	µA
I <sub>OZPD</sub> ‡	V <sub>CC</sub> = 2.1 V to 0, V <sub>O</sub> = 0.5 V to 2.7 V, $\overline{OE} = X$			±50		±10		±50	µA
I <sub>OZH</sub>	V <sub>CC</sub> = 2.1 V to 5.5 V, V <sub>O</sub> = 2.7 V, $\overline{OE} \geq 2 V$			10§		10		10§	µA
I <sub>OZL</sub>	V <sub>CC</sub> = 2.1 V to 5.5 V, V <sub>O</sub> = 0.5 V, $\overline{OE} \geq 2 V$			-10§		-10		-10§	µA
I <sub>off</sub>	V <sub>CC</sub> = 0, V <sub>I</sub> or V <sub>O</sub> ≤ 4.5 V			±100				±100	µA
I <sub>CEX</sub>	V <sub>CC</sub> = 5.5 V, V <sub>O</sub> = 5.5 V, Outputs high			50		50		50	µA
I <sub>O</sub> ¶	V <sub>CC</sub> = 5.5 V, V <sub>O</sub> = 2.5 V	-50	-140	-225§	-50	-225§	-50	-225§	mA
I <sub>CC</sub>	V <sub>CC</sub> = 5.5 V, I <sub>O</sub> = 0, V <sub>I</sub> = V <sub>CC</sub> or GND	Outputs high	80	250		250		250	µA
		Outputs low	35	40§		40§		40§	mA
		Outputs disabled	80	250		250		250	µA
ΔI <sub>CC</sub> #	V <sub>CC</sub> = 5.5 V, One input at 3.4 V, Other inputs at V <sub>CC</sub> or GND	Outputs enabled		1.5		1.5		1.5	mA
		Outputs disabled		50		50		50	µA
		Control inputs		1.5		1.5		1.5	mA
C <sub>i</sub>	V <sub>I</sub> = 2.5 V or 0.5 V		4					pF	
C <sub>o</sub>	V <sub>O</sub> = 2.5 V or 0.5 V		8					pF	

\* On products compliant to MIL-PRF-38535, this parameter does not apply.

† All typical values are at V<sub>CC</sub> = 5 V.

‡ This parameter is characterized, but not production tested.

§ This data sheet limit may vary among suppliers.

¶ Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

# This is the increase in supply current for each input that is at the specified TTL voltage level rather than V<sub>CC</sub> or GND.

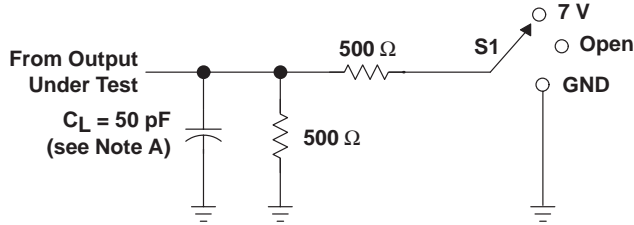
**switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C<sub>L</sub> = 50 pF (unless otherwise noted) (see Figure 1)**

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 5 V, T <sub>A</sub> = 25°C			SN54ABT827		SN74ABT827		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t <sub>PLH</sub>	A	Y	1.1	2.6	4.4	1.1	4.9	1.1	4.8	ns
t <sub>PHL</sub>			1.1	2.3	4.1	1.1	4.8	1.1	4.7	
t <sub>PZH</sub>	$\overline{OE}$	Y	1§	3.2	5.1	1	6	1§	5.9	ns
t <sub>PZL</sub>			1§	3.3	5.9	1	7.1	1§	6.9	
t <sub>PHZ</sub>	$\overline{OE}$	Y	2	4.9	6.3	2	7	2	6.8	ns
t <sub>PLZ</sub>			1.3§	4.2	6.6	1.3	7.9	1.3§	6.9	

§ This data sheet limit may vary among suppliers.

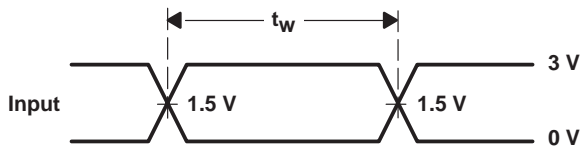


PARAMETER MEASUREMENT INFORMATION

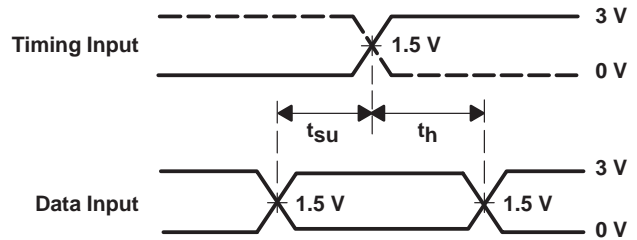


LOAD CIRCUIT

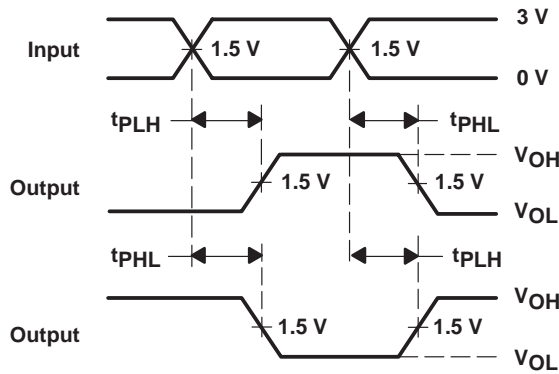
TEST	S1
$t_{PLH}/t_{PHL}$	Open
$t_{PLZ}/t_{PZL}$	7 V
$t_{PHZ}/t_{PZH}$	Open



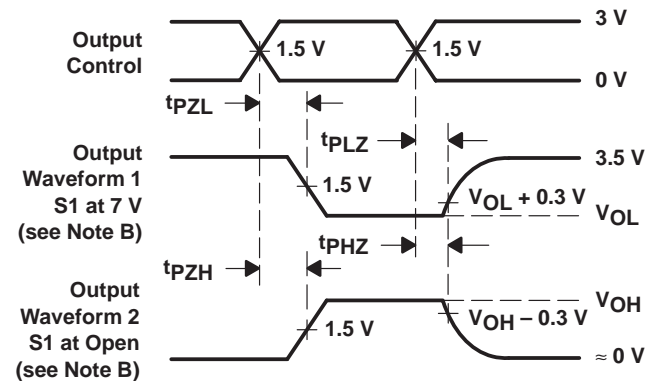
VOLTAGE WAVEFORMS  
PULSE DURATION



VOLTAGE WAVEFORMS  
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS  
PROPAGATION DELAY TIMES  
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS  
ENABLE AND DISABLE TIMES  
LOW- AND HIGH-LEVEL ENABLING

- NOTES: A.  $C_L$  includes probe and jig capacitance.  
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.  
C. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10$  MHz,  $Z_O = 50 \Omega$ ,  $t_r \leq 2.5$  ns,  $t_f \leq 2.5$  ns.  
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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